

D. Czekaj, A. Lisińska-Czekaj

*Gdańsk University of Technology, Faculty of Mechanical Engineering, Department of Materials Engineering and Welding, 80-233, Gdańsk, Poland
dionizy.czekaj@pg.edu.pl*

INFLUENCE OF DOPANTS ON STRUCTURE OF POLYCRYSTALLINE BISMUTH NIOBATE

ABSTRACT

Bismuth niobate (BiNbO_4) has attracted attention as a low-fired ceramics with promising microwave application potential. BiNbO_4 ceramics was fabricated by mixed oxide method and sintered at temperature $T < 1000^\circ\text{C}$. As the sintering aids a small amount of CuO oxide was used. The crystalline structure of the ceramic samples was examined by X-ray diffraction method at room temperature. The Rietveld refinement method was used for analysis of diffraction data. As a result an influence of dopants on crystal structure of bismuth niobate (BiNbO_4) ceramics was revealed. It was found that fabricated BiNbO_4 ceramics adopted the orthorhombic symmetry (α - BiNbO_4 phase, $Pnna$ (52) space group). Small differences in elementary cell parameters were found.

Keywords: BiNbO₄ ceramics, X-ray diffraction, phase analysis, crystal structure

INTRODUCTION

Rapid development of the mobile telecommunication has caused an increasing effort towards further miniaturization of microwave devices [1]. In order to miniaturize devices of band pass filters and antenna duplexers, multilayer microwave devices have been investigated. Realization of these devices may be accomplished by integration of passive components such as capacitors, resistors, inductors and line resonators into the substrate carrying the integrated circuits. In this connection it should be noted that such “passive integration” is performed using multilayer ceramics technology, whereby green ceramic tapes of different materials are laminated and co-fired usually at rather low temperatures ($T < 1000^\circ\text{C}$) with low loss and low melting point electrode such as Ag or Cu [1].

For microwave ceramics, it is desirable to have a high dielectric constant, a small temperature coefficient of resonant frequency, and high quality factor. The dielectric constant determines the size of the dielectric resonator operating at a given frequency, the temperature coefficient of resonant frequency expresses the variation of resonant frequency with the change in temperature, and the quality factor is the figure of merit, which reflects the dielectric loss of ceramics and is inversely proportional to bandwidth [2].

On the other hand, most of the known commercial microwave dielectrics such as complex perovskite compounds: $\text{Sn}_x\text{Zr}_{1-x}\text{TiO}_3$, $\text{Ba}(\text{Zn}_{1/3}\text{Ta}_{2/3})\text{O}_3$ (BZT) and $\text{Ba}(\text{Mg}_{1/3}\text{Ta}_{2/3})\text{O}_3$ (BMT) that exhibit excellent microwave dielectric properties, can be sintered only at very

high temperatures greater than 1400°C. Therefore, it is necessary to find the microwave dielectric ceramics with low sintering temperatures. An extensive overview of most known microwave dielectric materials is available elsewhere [e.g. 3].

Bismuth niobate (BiNbO_4) has been reported to be a promising microwave dielectric due to its high quality factor ($Q=14000$), small temperature coefficient of resonance frequency (~ 50 ppm/°C), and relatively low dielectric constant (~ 45) [4].

BiNbO_4 belongs to the bismutocolumbite oxides with similarly to scheelite-like stibiotantalite structure (SbTaO_4) $\text{A}^{3+}\text{B}^{5+}\text{O}_4$. It exhibits a triclinic phase (β), when the sintering temperature is increased above 1020°C (Fig. 1a) and an orthorhombic structure (α) when the sintering temperature is about 900°C (Fig. 1b) [5].

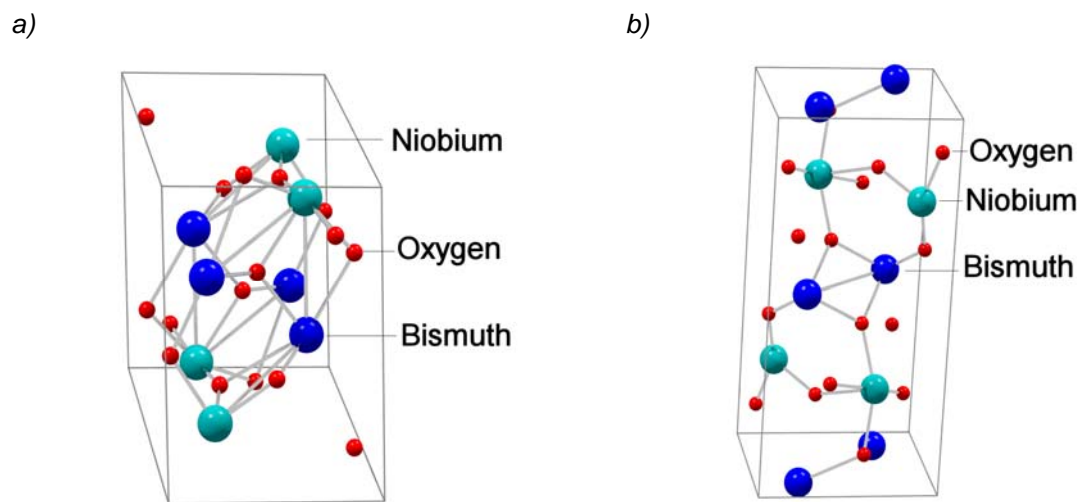


Fig. 1. Models of BiNbO_4 crystal structure for the high-temperature triclinic β -phase (a) and the low-temperature orthorhombic α -phase (b)

It is worth noting that various attempts have been undertaken to improve the microwave dielectric properties of BiNbO_4 , such as the substitution of lanthanide for Bi [e.g. 6, 7], the solid solutions of $\text{Bi}(\text{Nb}_{1-x}\text{Ta}_x)\text{O}_4$, $\text{Bi}(\text{Nb}_{1-x}\text{Sb}_x)\text{O}_4$ and the addition of various sintering aids like Bi_2O_3 [8], CuO [9], V_2O_5 [10] or $\text{CuO-V}_2\text{O}_5$ mixtures [11, 12]. However, the effect of the additives on structural characteristics of BiNbO_4 ceramics was not reported. It is interesting to clarify the above relationship because as it is commonly known [e.g. 13], the crystal structure determines the properties of the materials, especially microwave dielectric properties.

Aim of the present research was to study an influence of CuO dopant on crystal structure of BiNbO_4 ceramics fabricated by mixed oxide method followed by pressureless sintering at temperature $T < 1000^\circ\text{C}$.

EXPERIMENTAL

BiNbO_4 ceramics used for structural characterization in the present study was synthesized using solid state reaction method from the mixture of oxide powders (mixed oxide method). The appropriate amounts of reagent – grade oxide powders, viz. Bi_2O_3 and Nb_2O_5 were thoroughly weighted in stoichiometric amounts to provide conditions for formation of the desired composition, given in Eq. (1):



In the present study four sets of BiNbO_4 ceramic samples were fabricated, namely the stoichiometric one, the one containing an excess of 2.5wt% of CuO.

Then the mixture of oxides was ground with an agate mortar and pestle first. After that the planetary ball mill was utilized for wet grinding of the powders. A small amount of ethyl alcohol and zirconia balls as grinding medium were used in the milling/homogenizing treatment that lasted for $t=24\text{h}$. After milling the powders were subjected for drying. When dried the mixture of powders was compacted into pellets of 20 mm in diameter by pressing under pressure of $p=30\text{ MPa}$ in a stainless – steel die. The green bodies were then placed in an alumina crucible and fired with air at $T=800^\circ\text{C}$ (the heating rate $^\circ\text{C}/\text{min}$, the soaking time $t=2\text{h}$) to conduct the solid state reaction. After thermal treatment the pellets were crushed in a mortar and the synthesized material was subjected to wet milling and drying again. Before final sintering the compacts were formed in a stainless – steel die of 10 mm in diameter. Final sintering was performed by pressureless sintering under ambient air in a furnace at temperature $T=910^\circ\text{C}$ and soaking time $t=2\text{h}$. Thus fabricated BiNbO_4 ceramics were characterized in terms of phase composition, microstructure and crystal structure. Details of the preparation method as well as results of simultaneous thermal analysis (STA) of the powders, have been reported by us elsewhere [14, 15].

The phase composition as well as the crystal structure of powdered ceramics were studied by X-ray diffraction method at room temperature (X'Pert – Pro diffractometer, $\Theta - 2\Theta$ mode, $\text{CoK}\alpha$ or $\text{CuK}\alpha$ radiation, detector scan step $\Delta 2\Theta=0.01^\circ$ and a counting time $t=100\text{s}$). Phase analysis of X-ray diffraction patterns of BiNbO_4 powders was carried out using Match! (Crystal Impact) computer program [16]. The structural analysis was performed with X'pert HighScore Plus software (PANalytical B.V). The latest available ICSD [17], ICDD [18] and IUCr/COD/AMCSD [19], databases were utilized. Refinement of the structural parameters of BiNbO_4 ceramics was performed with the Rietveld method [e.g. 20].

RESULTS AND DISCUSSION

Morphology of BiNbO_4 ceramics sintered at $T_s=910^\circ\text{C}$ with stoichiometric composition and with CuO additive are shown in Fig. 2. One can see in from Fig. 2 that CuO additive has a substantial influence on morphology of BiNbO_4 ceramics. Application of CuO as a sintering aid decreased porosity of the ceramic samples under study.

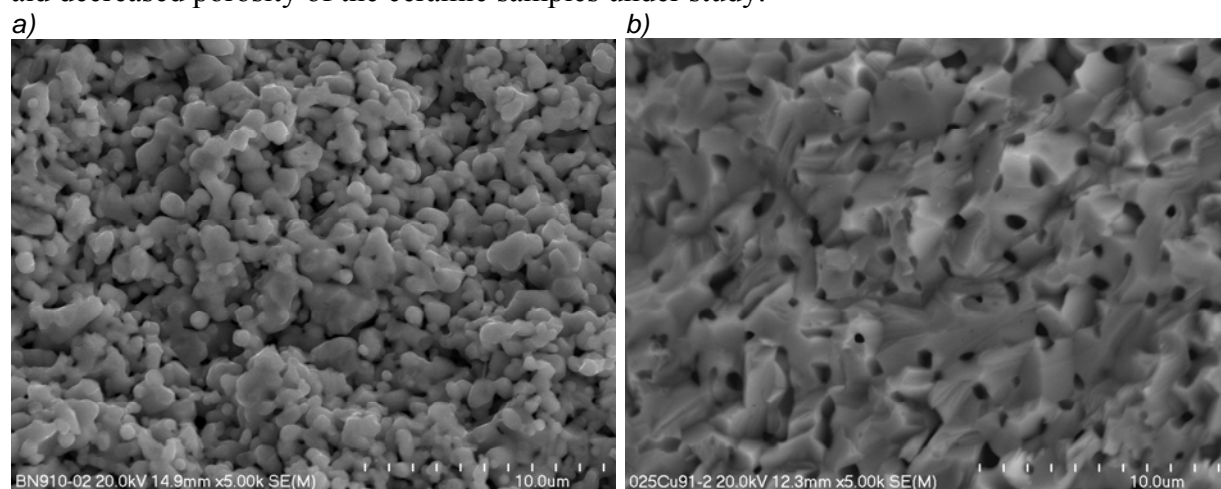


Fig. 2. Morphology of BiNbO_4 ceramics sintered at $T_s=910^\circ\text{C}$ with stoichiometric composition (a) and with 2.5wt% of CuO additive (b)

Results of the X-ray phase analysis performed for all compositions under study have proved that BiNbO_4 compound with orthorhombic structure was fabricated. As an example Fig. 3 illustrates results of the phase analysis of BiNbO_4 ceramics modified with 2.5wt% of CuO .

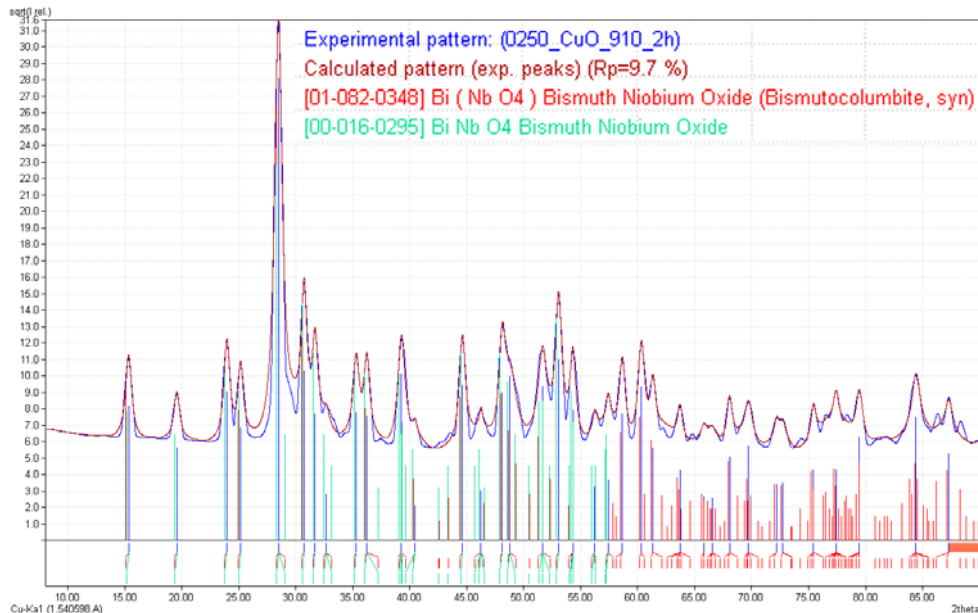


Fig. 3. Results of X-ray phase analysis of BiNbO_4 modified with 2.5wt % of CuO oxide. Miller indices (hkl) are not shown to increase visibility of diffraction lines

It should be noted that figure of merit (*FOM* - a number which is calculated from the various measures of agreement between database and unknown pattern) showing quality of the phase identification was $FOM=83.65\%$ for powder diffraction standard PDF 01-082-0348 (bismutocolumbite, syn) and $FOM=82.85\%$ for PDF 00-016-0295 (bismuth niobium oxide). The best value of $FOM=86.89\%$ was achieved for PDF 01-082-0348 standard while BiNbO_4 ceramics fabricated from stoichiometric mixture of oxides was studied.

Comparison of X-ray diffraction patterns recorded at room temperature for the samples of BiNbO_4 ceramics sintered at $T=910^\circ\text{C}$ without and with CuO additive is given in Fig. 4.

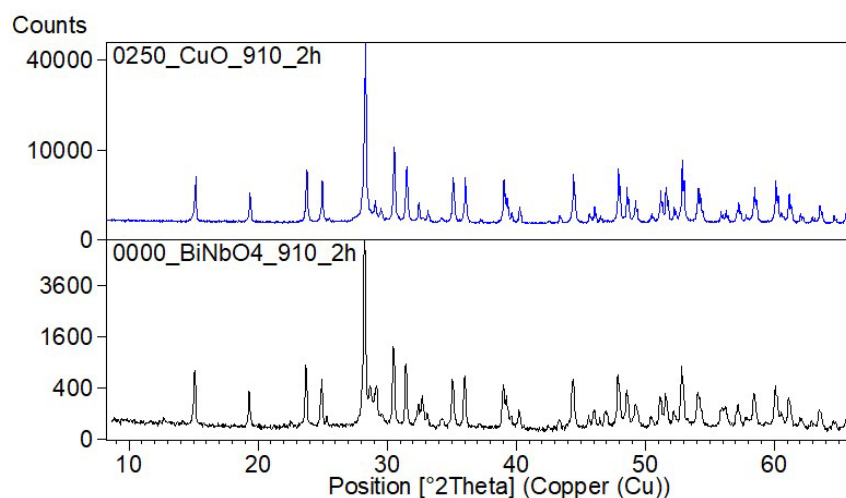


Fig. 4. Comparison of X-ray diffraction patterns of BiNbO_4 ceramics sintered at $T=910^\circ\text{C}$ with 2.5 wt.% of CuO additive and without any additives (i.e. stoichiometric composition) - from top to bottom, respectively

One can see from Fig. 4 that X-ray powder diffraction patterns are almost identical. The detailed analysis based on the Rietveld refinement method [20] was performed and the resultant X-ray diffraction pattern for CuO modified BiNbO₄ is given in Fig. 5.

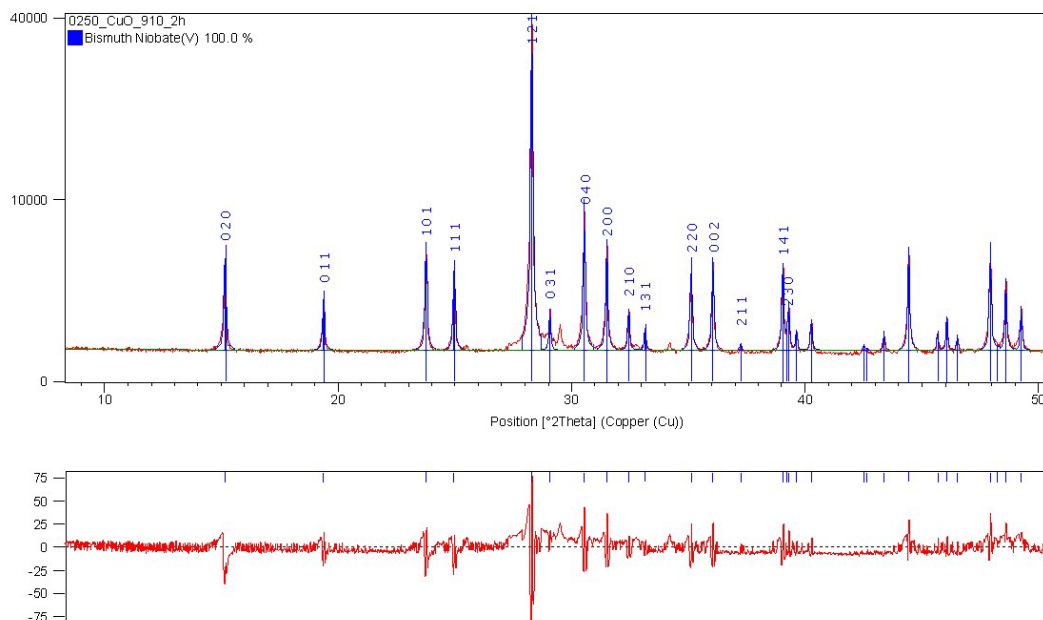


Fig. 5. X-ray diffraction pattern of BiNbO₄ ceramics modified with 2.5wt% of CuO oxide

The calculations have shown that BiNbO₄ ceramics sintered at $T=910^{\circ}\text{C}$ without additives as well as with 2.5 wt% of CuO additive exhibits orthorhombic structure described with *Pnna* (52) space group. However, the differences in structural characteristics were found (Fig. 6).

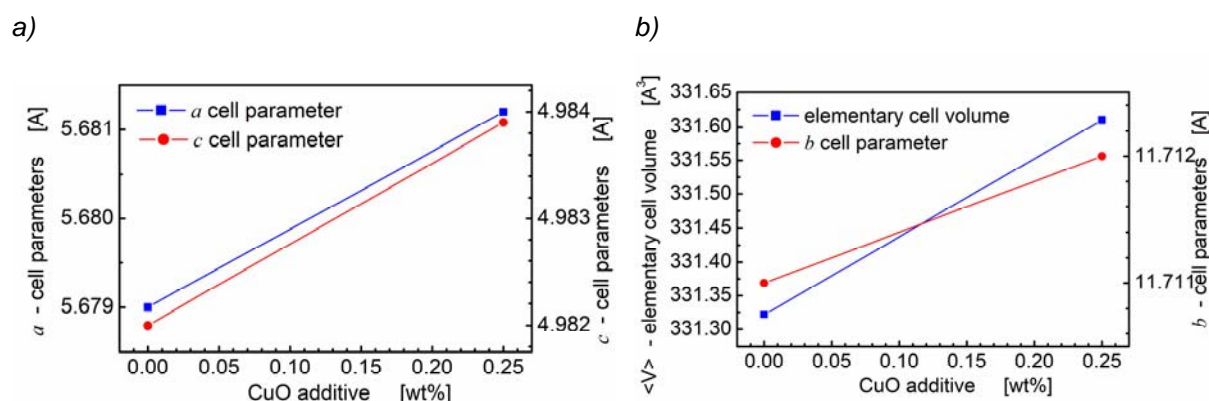


Fig. 6. Dependence of elementary cell parameters and elementary cell volume of BiNbO₄ ceramics on CuO additive

One can see from Fig. 6 that 2.5wt% of CuO additive led to an increase in the elementary cell parameters. It means that apart from the sintering aid effect (due to low melting point of CuO) that was visible in a less porous microstructure of the sintered ceramics (Fig. 2) Cu can act as an element substituting either bismuth (Bi) [9] or niobium (Nb) in amount considering the electrovalence balance and ionic radii.

CONCLUSION

By means of mixed oxide method and pressureless sintering in ambient atmosphere BiNbO₄ ceramics was fabricated. The influence of the small amount of CuO additive on microstructure and crystal structure of BiNbO₄ ceramic was investigated. A substantial influence of 2.5wt% of CuO on morphology of BiNbO₄ ceramics was found. The additive decreased porosity of ceramic samples but lots of cracks were created in the grain due to CuO evaporation. It was also found that 2.5wt% of CuO additive did not cause any change of the crystal symmetry of the BiNbO₄ ceramics. BiNbO₄ crystallized in the orthorhombic symmetry (α -BiNbO₄ phase, *Pnna* (52) space group). However, it was found that additive led to an increase in the elementary cell parameters and thus increases volume of the orthorhombic elementary cell.

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